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LIST OF DOCUMENTS CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT

M. ISHIBASHI et al

FILING DATE

January 18, 2002

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
P/L	AA	5,666,190	09/09/97	Quate et al			
P/L	AB	5,049,461	09/17/91	Arnett et al			
P/L	AC	5,546,375	8/13/96	Shimada et al			
P/L	AD	5,793,040	08/11/98	Oguchi et al			
P/L	AE	5,546,374	08/13/96	Kuroda et al			
P/L	AF	5,536,988	07/16/96	Zhange et al			
P/L	AG	5,431,055	07/11/95	Takata et al			
P/L	AH	5,150,392	09/22/92	Hohn et al			
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AL						<input type="checkbox"/>	<input type="checkbox"/>
	AM						<input type="checkbox"/>	<input type="checkbox"/>
	AN						<input type="checkbox"/>	<input type="checkbox"/>
	AO						<input type="checkbox"/>	<input type="checkbox"/>
	AP						<input type="checkbox"/>	<input type="checkbox"/>

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

P/L	AR		APPLIED PHYSICS LETTERS, Vol. 66, No. 6, Feb 6, 1995, "Fabrication of 0.1um metal oxide semiconductor field-effect transistors with the atomic force microscope," S.C. Minne et al, pp. 703-705.					
P/L	AS		1997 SYMPOSIUM ON VLSI TECHNOLOGY, "Fabrication on 100nm pMOSFETs with Hybrid AFN/STM Lithography", Soh et al.					
	AT							

EXAMINER

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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.